SN74LVC2G66 双路双边模拟开关

1 特性

- 采用德州仪器 (TI) 的 NanoFree™封装
- 1.65V 至 5.5V V运行
- 输入接受的电压达到 5.5V
- 电压为 3.3V 时，t_{pd} 最大值为 0.8ns
- 高开关输出电压比
- 高度线性
- 高速，典型值 0.5ns (V_{CC}=3V，C_L=50pF)
- 轨至轨输入/输出
- 低导通电阻，典型值为 ≠6 Ω (V_{CC} = 4.5V)
- 锁断性能超过 100mA，符合 JESD 78 II 类规范的要求

2 应用

- 无线设备
- 音频和视频信号路由
- 便携式计算
- 可穿戴设备
- 信号门控、斩波、调制或解调（调制解调器）
- 适用于模数和数模转换系统的信号多路复用

3 说明

该双路双向模拟开关适用于 1.65V 至 5.5V V_{CC} 运行环境。

SN74LVC2G66 器件可处理模拟信号和数字信号。SN74LVC2G66 器件允许在任意方向传输振幅高达 5.5V（峰值）的信号。

NanoFree 封装技术是 IC 封装概念上的一项重大突破，它将裸片用作封装。

每个开关部分有其自己的输入使能控制 (C)。应用到 C 上的一个高电平电压开启相关开关部分。

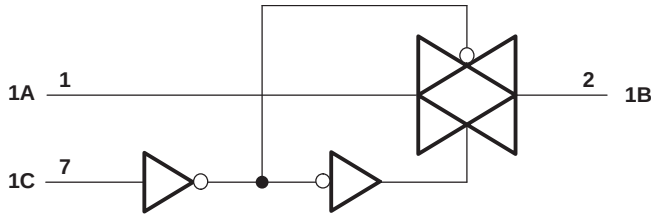
应用 包括信号门控、斩波、调制或解调（调制解调器）以及适用于模数和数模转换系统的信号多路复用。

器件信息(1)

器件型号	封装	封装尺寸（标称值）
SN74LVC2G66DCT	SSOP (8)	2.95mm × 2.80mm
SN74LVC2G66DCU	超薄小外形尺寸封装 (VSSOP)(8)	2.30mm x 2.00mm
SN74LVC2G66YZP	DSBGA (8)	1.91mm × 0.91mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

逻辑图、每次转换（正逻辑）



One of Two Switches

本文档旨在为方便起见，提供有关 TI 产品中文版本的信息，以确认产品的概要。 有关适用的官方英文版本的最新信息，请访问 www.ti.com，其内容始终优先。 TI 不保证翻译的准确性和有效性。 在实际设计之前，请务必参考最新版本的英文版本。

目录

4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision M (May 2018) to Revision N — **Page**

- Changed the YZP pin configuration 3

Changes from Revision L (September 2015) to Revision M — **Page**

- Updated pinout image and the *Pin Function* table 3
- Changed pin 3 Name From: 1C To: 2C 3
- Changed the *Thermal Information* table for the DCT package 5

Changes from Revision K (January 2014) to Revision L — **Page**

- 添加了*应用* 部分、*器件信息* 表、*引脚配置和功能* 部分、*ESD 额定值* 表、*典型值* 部分、*特性 说明* 部分、*器件功能模式*、*应用和实施* 部分、*电源建议* 部分、*布局* 部分、*器件和文档支持* 部分以及*机械、封装和可订购信息* 部分 1
- Added *Thermal Information* table 5

Changes from Revision J (December 2011) to Revision K — **Page**

- 将文档更新为新的 TI 数据表格式 - 规格没有变化。 1
- 删除了*订购信息* 表。 1

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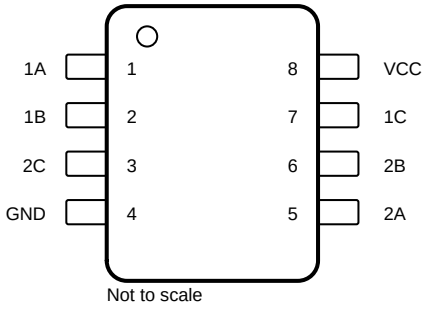
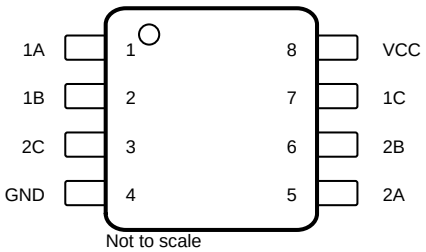
5 Pin Configuration and Functions

DCT Package
8-Pin SSOP
Top View



Not to scale

DCU Package
8-Pin VSSOP
Top View



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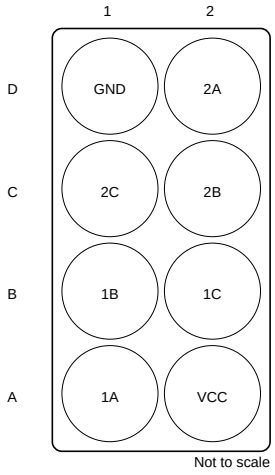
YZP Package
8-Pin DSBGA
Bottom View



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See mecahnical drawings for dimensions.

Pin Functions

PIN			I/O	DESCRIPTION
NAME	DCT DCU	YZP		
1A	1	A1	I/O	Bidirectional signal to be switched
1B	2	B1	I/O	Bidirectional signal to be switched
2C	3	C1	I	Controls the switch (L = OFF, H = ON)
2A	5	D2	I/O	Bidirectional signal to be switched
2B	6	C2	I/O	Bidirectional signal to be switched
1C	7	B2	I	Controls the switch (L = OFF, H = ON)
GND	4	D1	—	Ground pin
V_{CC}	8	A2	—	Power pin

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6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage(2)		–0.5	6.5	V
V_I	Input voltage(2)(3)		–0.5	6.5	V
V_O	Switch I/O voltage(2)(3)(4)		–0.5	V_{CC} + 0.5	V
I_{IK}	Control input clamp current	V_I < 0		–50	mA
$I_{I/OK}$	I/O port diode current	$V_{I/O}$ < 0 or $V_{I/O}$ > V_{CC}		–50	mA
I_T	On-state switch current	$V_{I/O}$ = 0 to V_{CC}		±50	mA
	Continuous current through V_{CC} or GND			±100	mA
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltages are with respect to ground, unless otherwise specified.
(3) The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
(4) This value is limited to 5.5 V maximum.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins(1)	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101, all pins(2)	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

See (1).

			MIN	MAX	UNIT
V_{CC}	Supply voltage		1.65	5.5	V
$V_{I/O}$	I/O port voltage		0	V_{CC}	V
V_{IH}	High-level input voltage, control input	V_{CC} = 1.65 V to 1.95 V	V_{CC} × 0.65		V
		V_{CC} = 2.3 V to 2.7 V	V_{CC} × 0.7		
		V_{CC} = 3 V to 3.6 V	V_{CC} × 0.7		
		V_{CC} = 4.5 V to 5.5 V	V_{CC} × 0.7		
V_{IL}	Low-level input voltage, control input	V_{CC} = 1.65 V to 1.95 V		V_{CC} × 0.35	V
		V_{CC} = 2.3 V to 2.7 V		V_{CC} × 0.3	
		V_{CC} = 3 V to 3.6 V		V_{CC} × 0.3	
		V_{CC} = 4.5 V to 5.5 V		V_{CC} × 0.3	
V_I	Control input voltage		0	5.5	V
Δt/Δv	Input transition rise or fall time	V_{CC} = 1.65 V to 1.95 V		20	ns/V
		V_{CC} = 2.3 V to 2.7 V		20	
		V_{CC} = 3 V to 3.6 V		10	
		V_{CC} = 4.5 V to 5.5 V		10	
T_A	Operating free-air temperature		–40	85	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, SCBA004.

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6.4 Thermal Information

THERMAL METRIC[1]		SN74LVC2G66			UNIT
		DCT (SSOP)	DCU (VSSOP)	YZP (DSBGA)	
		8 PINS	8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	186.1	204.4	102	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	116.5	77	—	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	98.6	83.2	—	°C/W
ψ_{JT}	Junction-to-top characterization parameter	42.2	7.1	—	°C/W
ψ_{JB}	Junction-to-board characterization parameter	97.6	82.7	—	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a	n/a	—	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP[1]	MAX	UNIT
r_{on}	ON-state switch resistance	$V_I = V_{CC}$ or GND, $V_C = V_{IH}$ (see Figure 3 and Figure 1)	I_S = 4 mA	1.65 V		12.5	30	Ω
			I_S = 8 mA	2.3 V		9	20	
			I_S = 24 mA	3 V		7.5	15	
			I_S = 32 mA	4.5 V		6	10	
$r_{on(p)}$	Peak ON-state resistance	$V_I = V_{CC}$ to GND, $V_C = V_{IH}$ (see Figure 3 and Figure 1)	I_S = 4 mA	1.65 V		85	120[1]	Ω
			I_S = 8 mA	2.3 V		22	30[1]	
			I_S = 24 mA	3 V		12	20	
			I_S = 32 mA	4.5 V		7.5	15	
Δr_{on}	Difference of ON-state resistance between switches	$V_I = V_{CC}$ to GND, $V_C = V_{IH}$ (see Figure 3 and Figure 1)	I_S = 4 mA	1.65 V			7	Ω
			I_S = 8 mA	2.3 V			5	
			I_S = 24 mA	3 V			3	
			I_S = 32 mA	4.5 V			2	
$I_{S(off)}$	OFF-state switch leakage current	$V_I = V_{CC}$ and V_O = GND or V_I = GND and $V_O = V_{CC}$, $V_C = V_{IL}$ (see Figure 4)		5.5 V			±1	μA
							±0.1[1]	
$I_{S(on)}$	ON-state switch leakage current	$V_I = V_{CC}$ or GND, $V_C = V_{IH}$, V_O = Open (see Figure 5)		5.5 V			±1	μA
							±0.1[1]	
I_I	Control input current	$V_C = V_{CC}$ or GND		5.5 V			±1	μA
							±0.1[1]	
I_{CC}	Supply current	$V_C = V_{CC}$ or GND		5.5 V			10	μA
							1[1]	
ΔI_{CC}	Supply-current change	$V_C = V_{CC}$ – 0.6 V		5.5 V			500	μA
C_{ic}	Control input capacitance			5 V		3.5		pF
$C_{io(off)}$	Switch input / output capacitance			5 V		6		pF
$C_{io(on)}$	Switch input / output capacitance			5 V		14		pF

(1) T_A = 25°C

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6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 1.8 V ± 0.15 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd} (1)	A or B	B or A		2		1.2		0.8		0.6	ns
t_{en} (2)	C	A or B	2.3	10	1.6	5.6	1.5	4.4	1.3	3.9	ns
t_{dis} (3)	C	A or B	2.5	10.5	1.2	6.9	2	7.2	1.1	6.3	ns

(1) t_{PLH} and t_{PHL} are the same as t_{pd}. The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).
(2) t_{PZL} and t_{PZH} are the same as t_{en}.
(3) t_{PLZ} and t_{PHZ} are the same as t_{dis}.

6.7 Analog Switch Characteristics

T_A = 25°C

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V_{CC}	TYP	UNIT
Frequency response (switch on)	A or B	B or A	C_L = 50 pF, R_L = 600 Ω, f_{in} = sine wave (see Figure 6)	1.65 V	35	MHz
				2.3 V	120	
				3 V	175	
				4.5 V	195	
			C_L = 5 pF, R_L = 50 Ω, f_{in} = sine wave (see Figure 6)	1.65 V	>300	
				2.3 V	>300	
				3 V	>300	
				4.5 V	>300	
Crosstalk (1) (between switches)	A or B	B or A	C_L = 50 pF, R_L = 600 Ω, f_{in} = 1 MHz (sine wave) (see Figure 7)	1.65 V	–58	dB
				2.3 V	–58	
				3 V	–58	
				4.5 V	–58	
			C_L = 5 pF, R_L = 50 Ω, f_{in} = 1 MHz (sine wave) (see Figure 7)	1.65 V	–42	
				2.3 V	–42	
				3 V	–42	
				4.5 V	–42	
Crosstalk (control input to signal output)	C	A or B	C_L = 50 pF, R_L = 600 Ω, f_{in} = 1 MHz (square wave) (see Figure 8)	1.65 V	35	mV
				2.3 V	50	
				3 V	70	
				4.5 V	100	
Feedthrough attenuation (switch off)	A or B	B or A	C_L = 50 pF, R_L = 600 Ω, f_{in} = 1 MHz (sine wave) (see Figure 9)	1.65 V	–58	dB
				2.3 V	–58	
				3 V	–58	
				4.5 V	–58	
			C_L = 5 pF, R_L = 50 Ω, f_{in} = 1 MHz (sine wave) (see Figure 9)	1.65 V	–42	
				2.3 V	–42	
				3 V	–42	
				4.5 V	–42	

(1) Adjust f_{in} voltage to obtain 0 dBm at input.

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Analog Switch Characteristics (continued)

T_A = 25°C

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V_{CC}	TYP	UNIT
Sine-wave distortion	A or B	B or A	C_L = 50 pF, R_L = 10 kΩ, f_{in} = 1 kHz (sine wave) (see Figure 10)	1.65 V	0.1%	
				2.3 V	0.025%	
				3 V	0.015%	
				4.5 V	0.01%	
			C_L = 50 pF, R_L = 10 kΩ, f_{in} = 10 kHz (sine wave) (see Figure 10)	1.65 V	0.15%	
				2.3 V	0.025%	
				3 V	0.015%	
				4.5 V	0.01%	

6.8 Operating Characteristics

T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC} = 1.8 V	V_{CC} = 2.5 V	V_{CC} = 3.3 V	V_{CC} = 5 V	UNIT
			TYP	TYP	TYP	TYP	
C_{pd}	Power dissipation capacitance	f = 10 MHz	8	9	9.5	11	pF

6.9 Typical Characteristics

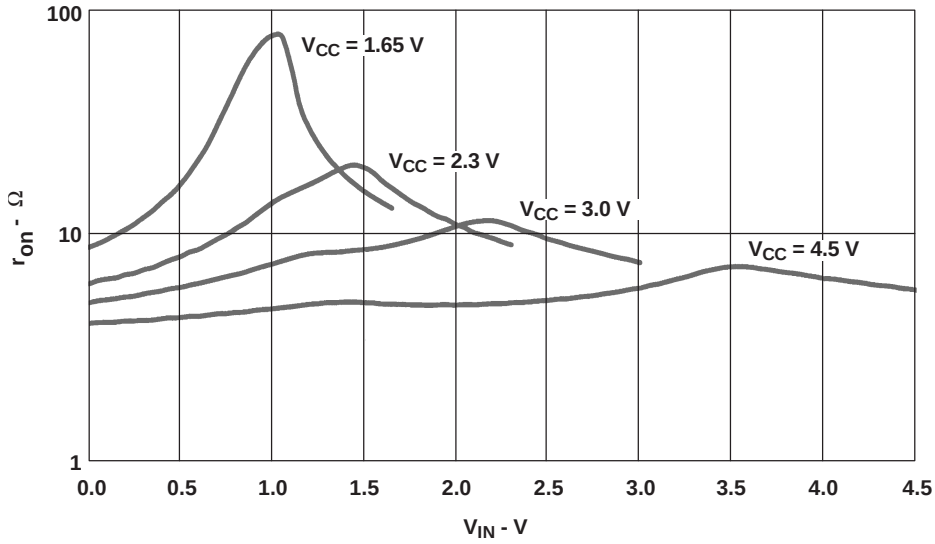

Figure 1. Typical r_{on} as a Function of Input Voltage (V_I) for V_I = 0 to V_{CC}

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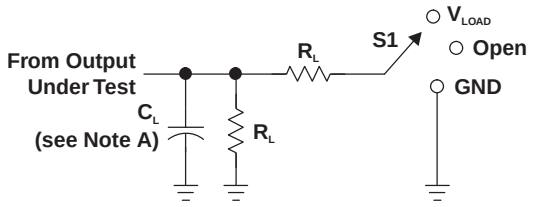
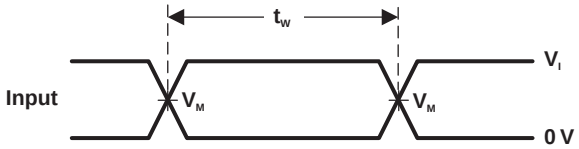
7 Parameter Measurement Information



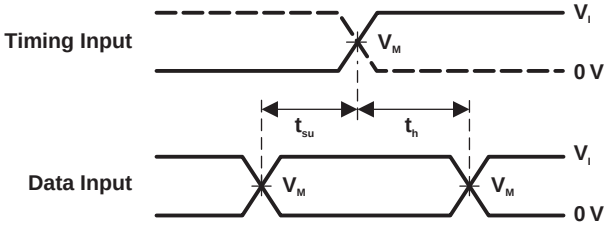
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

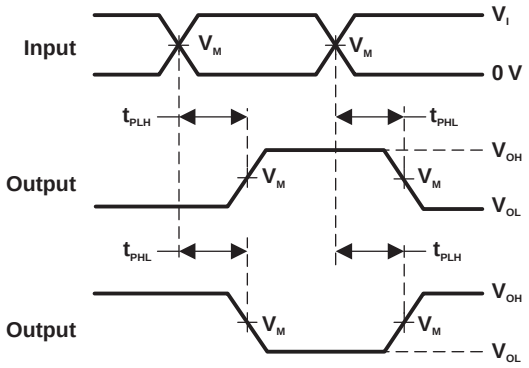
V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_Δ
	V_I	t_r/t_f					
1.8 V ± 0.15 V	V_{CC}	≤2 ns	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	1 kΩ	0.15 V
2.5 V ± 0.2 V	V_{CC}	≤2 ns	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	500 Ω	0.15 V
3.3 V ± 0.3 V	V_{CC}	≤2.5 ns	$V_{CC}/2$	$2 \times V_{CC}$	50 pF	500 Ω	0.3 V
5 V ± 0.5 V	V_{CC}	≤2.5 ns	$V_{CC}/2$	$2 \times V_{CC}$	50 pF	500 Ω	0.3 V



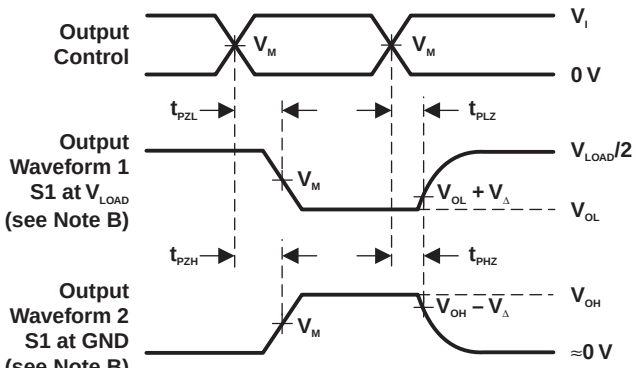
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators have the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω.
D. The outputs are measured one at a time, with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.
H. All parameters and waveforms are not applicable to all devices.

Figure 2. Load Circuit and Voltage Waveforms

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Parameter Measurement Information (continued)

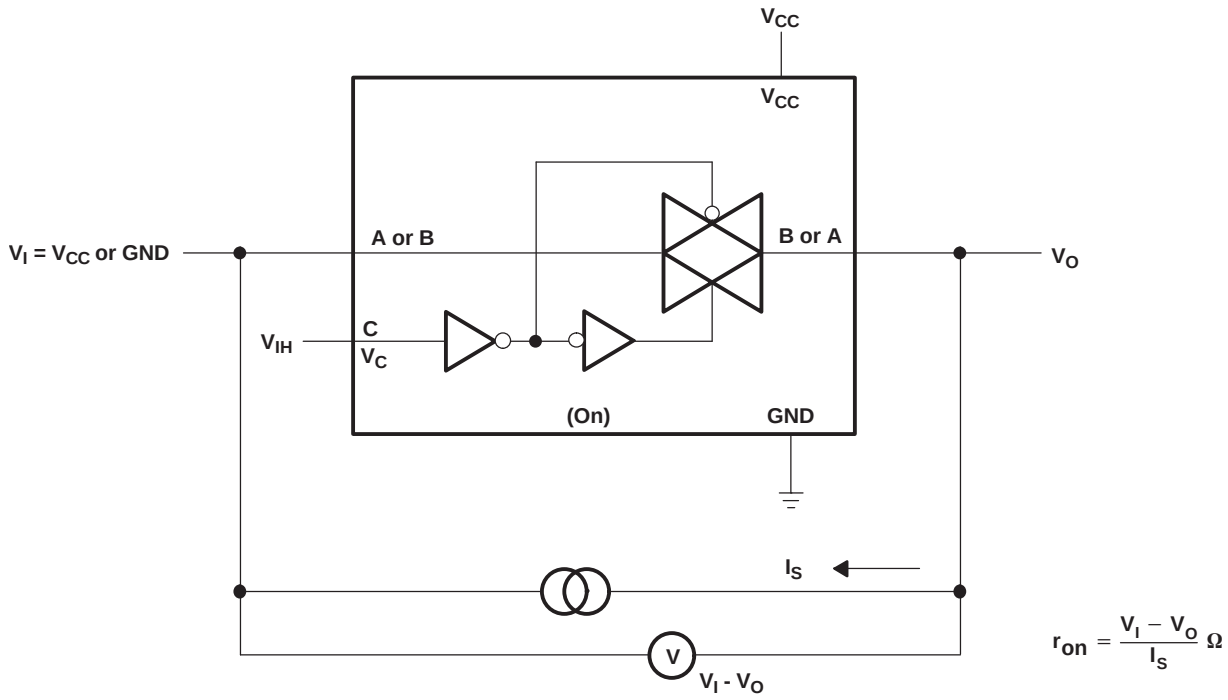

Figure 3. ON-State Resistance Test Circuit

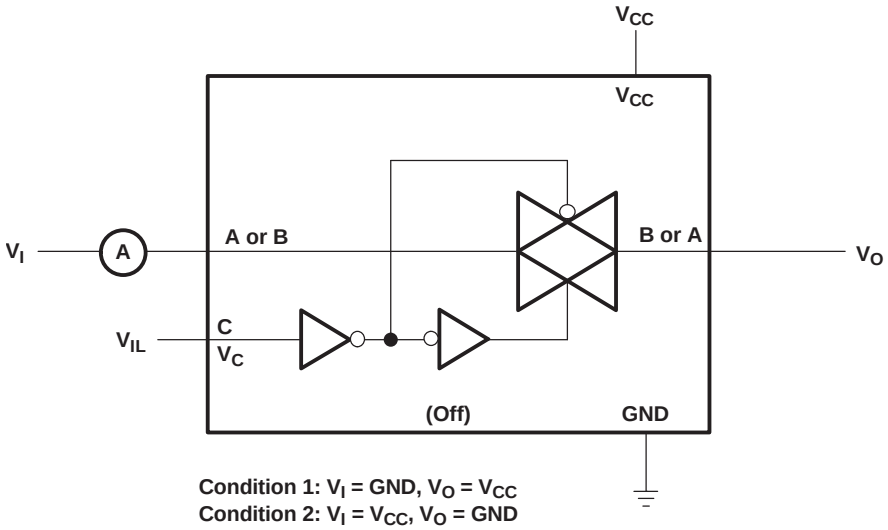

Figure 4. OFF-State Switch Leakage-Current Test Circuit

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Parameter Measurement Information (continued)

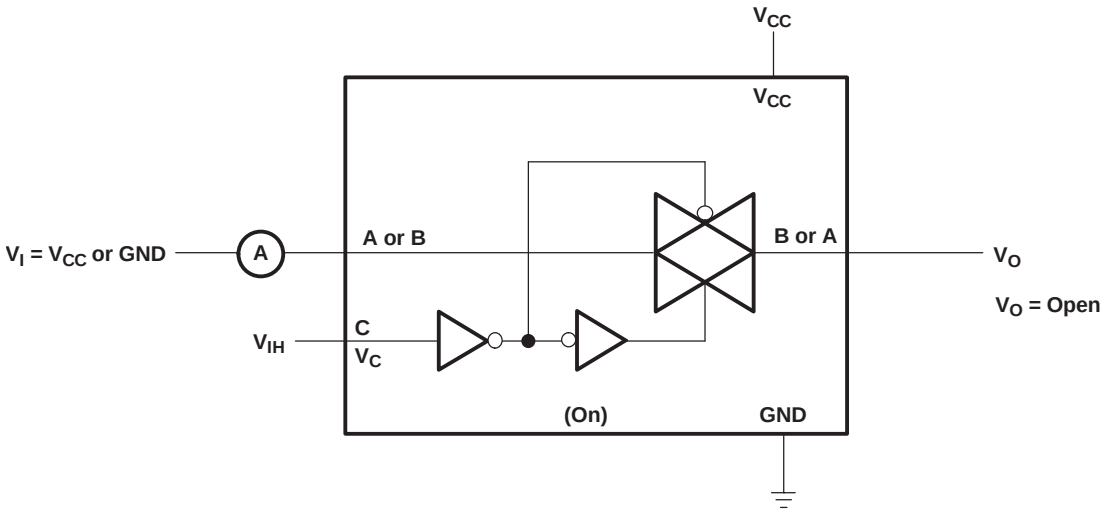

Figure 5. ON-State Leakage-Current Test Circuit

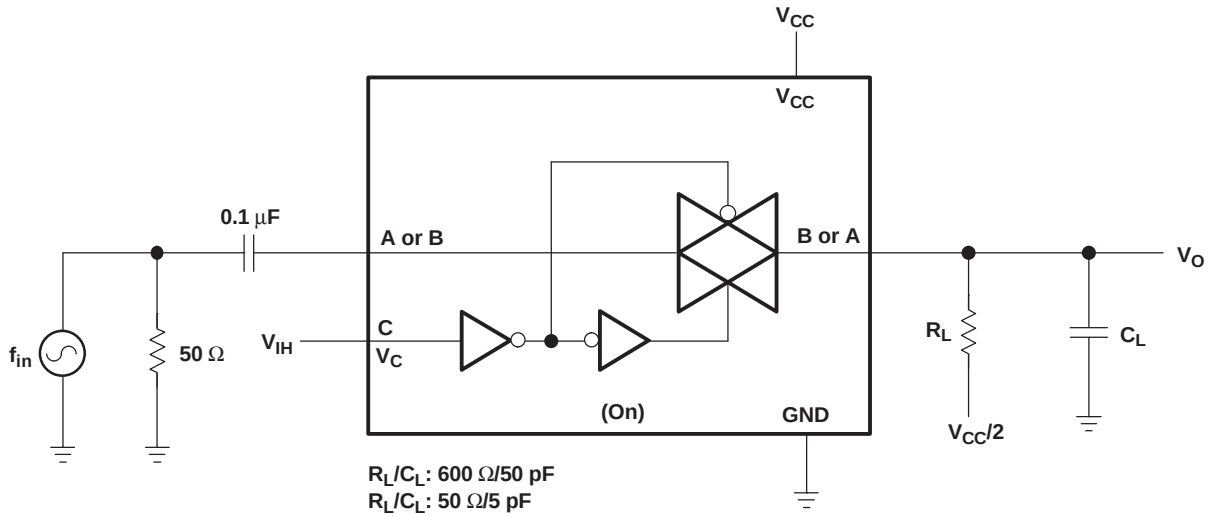

Figure 6. Frequency Response (Switch On)

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Parameter Measurement Information (continued)

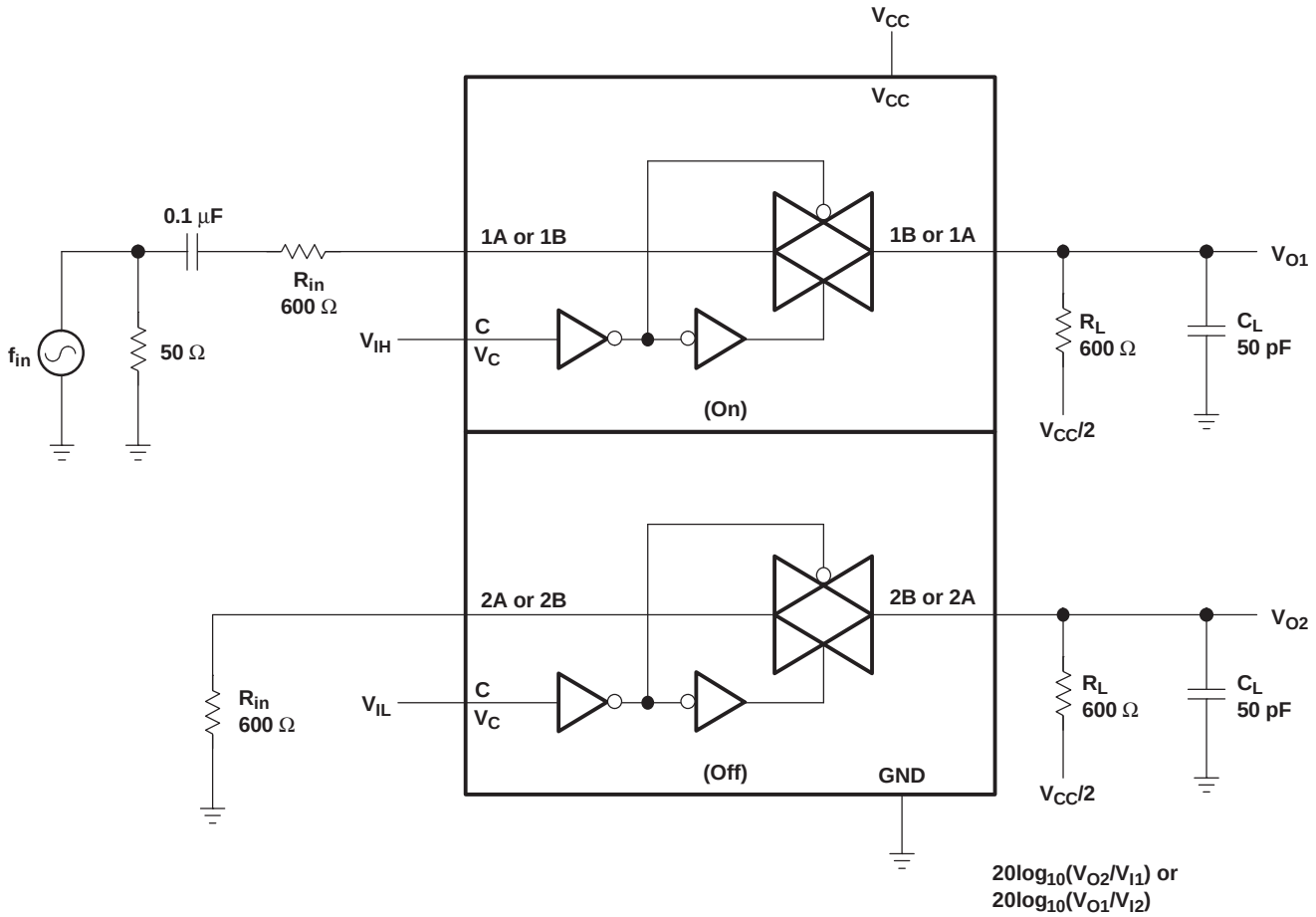

Figure 7. Crosstalk (Between Switches)

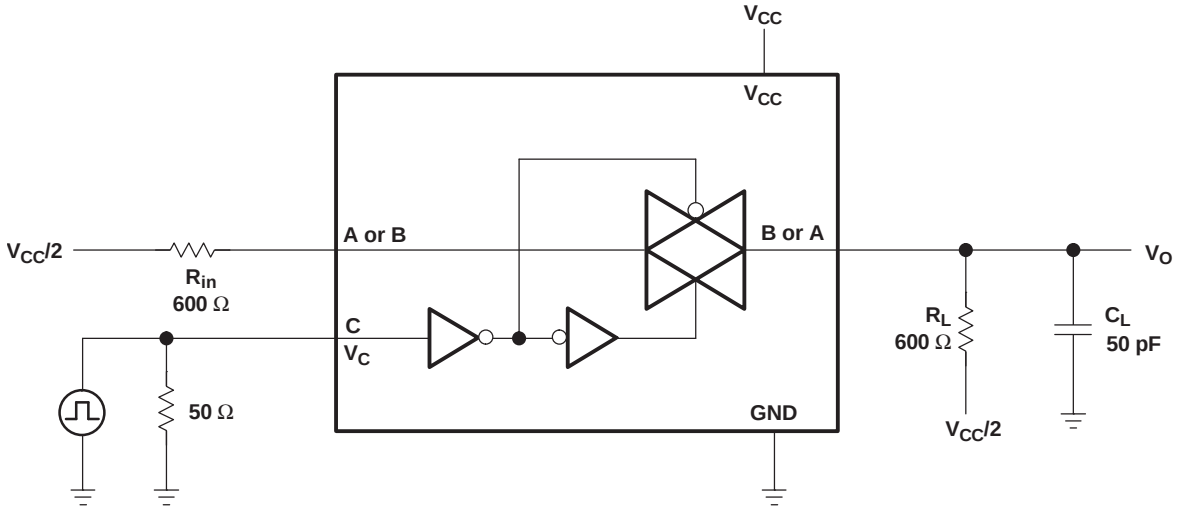

Figure 8. Crosstalk (Control Input, Switch Output)

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Parameter Measurement Information (continued)

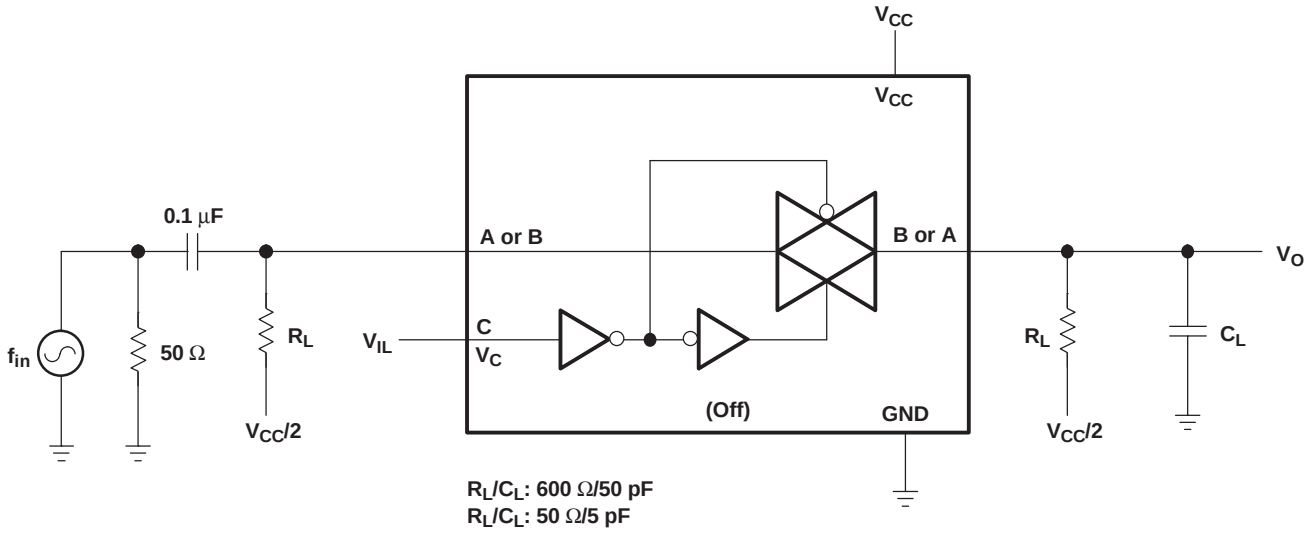

Figure 9. Feedthrough (Switch Off)

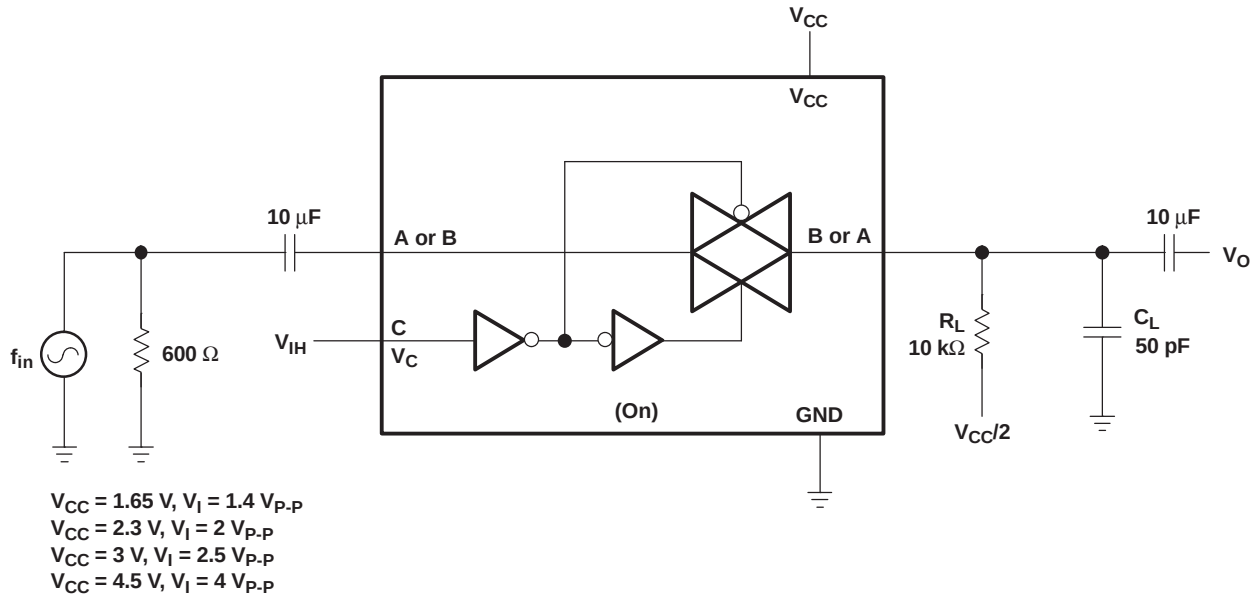

Figure 10. Sine-Wave Distortion

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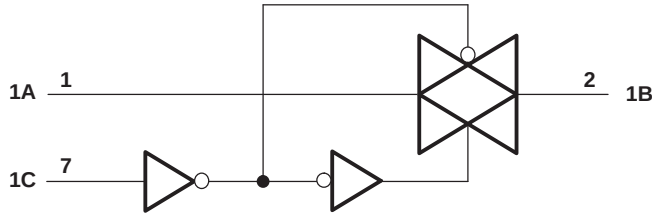
8 Detailed Description

8.1 Overview

This dual bilateral analog switch is designed for 1.65-V to 5.5-V V_{CC} operation. Robust LVC family technology allows this device to accept input voltages without connecting power to V_{CC}.

The SN74LVC2G66 device permits signals with amplitudes of up to 5.5 V (peak) to be transmitted in either direction. A high-level voltage applied to the control pin C enables the respective switch to begin propagating signals across the device. A low-level voltage disables this transmission. Each device incorporates two switches with independent control and operation.

8.2 Functional Block Diagram



One of Two Switches

8.3 Feature Description

Each switch section has its own enable-input control (C). A high-level voltage applied to C turns on the associated switch section. When C is this Signals can pass through A to B or B to A. Low ON-resistance of 6 Ω at 4.5-V V_{CC} is ideal for analog signal conditioning systems. The control signals can accept voltages up to 5.5 V without V_{CC} connected in the system. Combination of lower t_{pd} of 0.8 ns at 3.3 V and low enable and disable time make this part suitable for high-speed signal switching applications.

8.4 Device Functional Modes

Table 1 lists the functional modes of the SN74LVC2G66.

Table 1. Function Table

CONTROL INPUT (C)	SWITCH
L	Off
H	On

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9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74LVC2G66 can be used in any situation where an Dual SPST switch would be used and a solid-state, voltage controlled version is preferred.

9.2 Typical Application

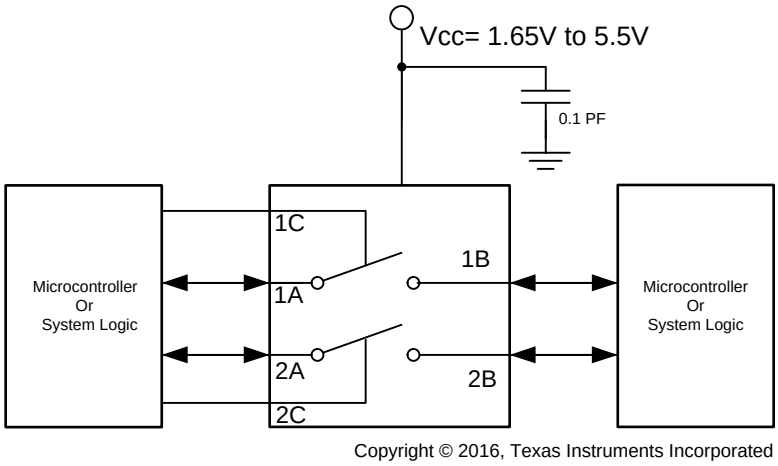

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Figure 11. Typical Application Schematic

9.2.1 Design Requirements

The SN74LVC2G66 allows on/off control of analog and digital signals with a digital control signal. All input signals should remain between 0 V and V_{CC} for optimal operation.

9.2.2 Detailed Design Procedure

1. Recommended Input Conditions:
   - For rise time and fall time specifications, see $\Delta t/\Delta v$ in the *Recommended Operating Conditions* table.
   - For specified high and low levels, see V_{IH} and V_{IL} in the *Recommended Operating Conditions* table.
   - Inputs and outputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid V_{CC}.
2. Recommended Output Conditions:
   - Load currents should not exceed ±50 mA.
3. Frequency Selection Criterion:
   - Maximum frequency tested is 150 MHz.
   - Added trace resistance or capacitance can reduce maximum frequency capability; use layout practices as directed in *Layout*.

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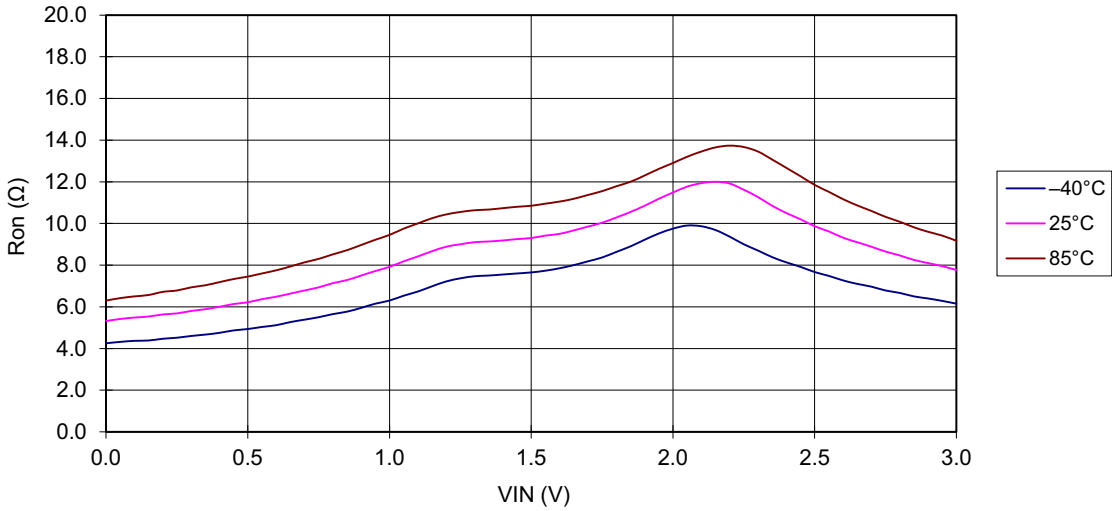
Typical Application (continued)

9.2.3 Application Curve



Pin: A–B, V_{CC} = 3 V, I_S = 24 mA

Figure 12. r_{on} vs V_I

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*.

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1-μF bypass capacitor is recommended. If there are multiple pins labeled V_{CC}, then a 0.01-μF or 0.022-μF capacitor is recommended for each V_{CC} because the VCC pins will be tied together internally. For devices with dual-supply pins operating at different voltages, for example V_{CC} and V_{DD}, a 0.1-μF bypass capacitor is recommended for each supply pin. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1-μF and 1-μF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

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11 Layout

11.1 Layout Guidelines

Reflections and matching are closely related to loop antenna theory, but different enough to warrant their own discussion. When a PCB trace turns a corner at a 90° angle, a reflection can occur. This is primarily due to the change of width of the trace. At the apex of the turn, the trace width is increased to 1.414 times its width. This upsets the transmission line characteristics, especially the distributed capacitance and self–inductance of the trace — resulting in the reflection.

NOTE

Not all PCB traces can be straight, and so they will have to turn corners. Figure 13 shows progressively better techniques of rounding corners. Only the last example maintains constant trace width and minimizes reflections.

11.2 Layout Example

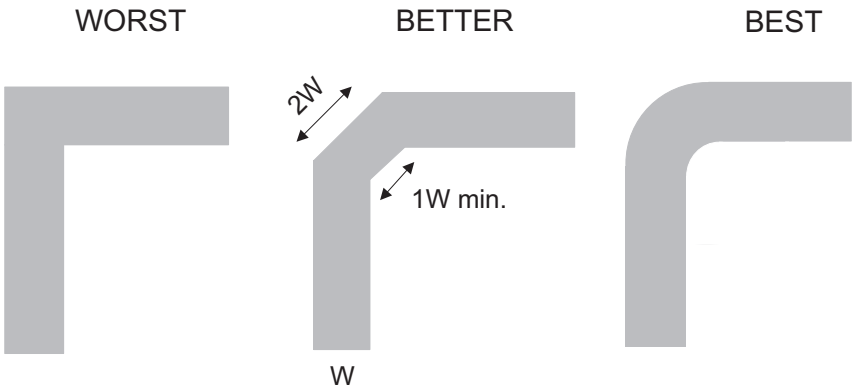

Figure 13. Trace Example

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12 器件和文档支持

12.1 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商“按照原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 《使用条款》。

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设计支持 ***TI 参考设计支持*** 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

12.2 商标

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12.3 静电放电警告

这些装置包含有限的内置 ESD 保护。 存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

12.4 术语表

SLYZ022 — *TI 术语表*。

这份术语表列出并解释术语、缩写和定义。

13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC2G66DCTR	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66 (R, Z)	Samples
SN74LVC2G66DCTRE4	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66 (R, Z)	Samples
SN74LVC2G66DCTRG4	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66 (R, Z)	Samples
SN74LVC2G66DCUR	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 85	(66, C66Q, C66R) CZ	Samples
SN74LVC2G66DCURG4	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66R	Samples
SN74LVC2G66DCUT	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 85	(C66Q, C66R)	Samples
SN74LVC2G66DCUTE4	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66R	Samples
SN74LVC2G66DCUTG4	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C66R	Samples
SN74LVC2G66YZPR	ACTIVE	DSBGA	YZP	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(C67, C6N)	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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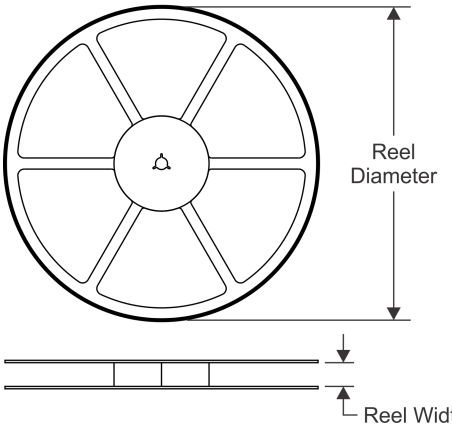
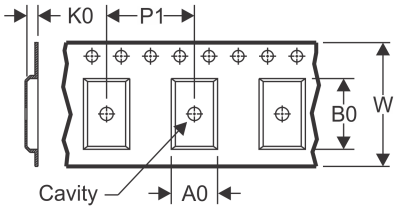
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

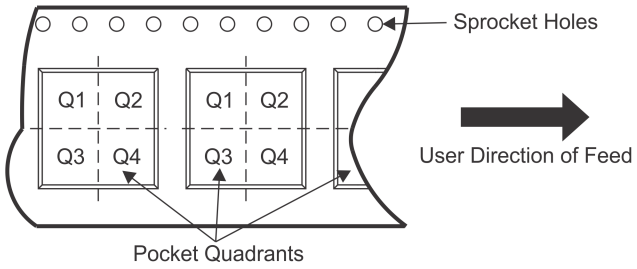


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

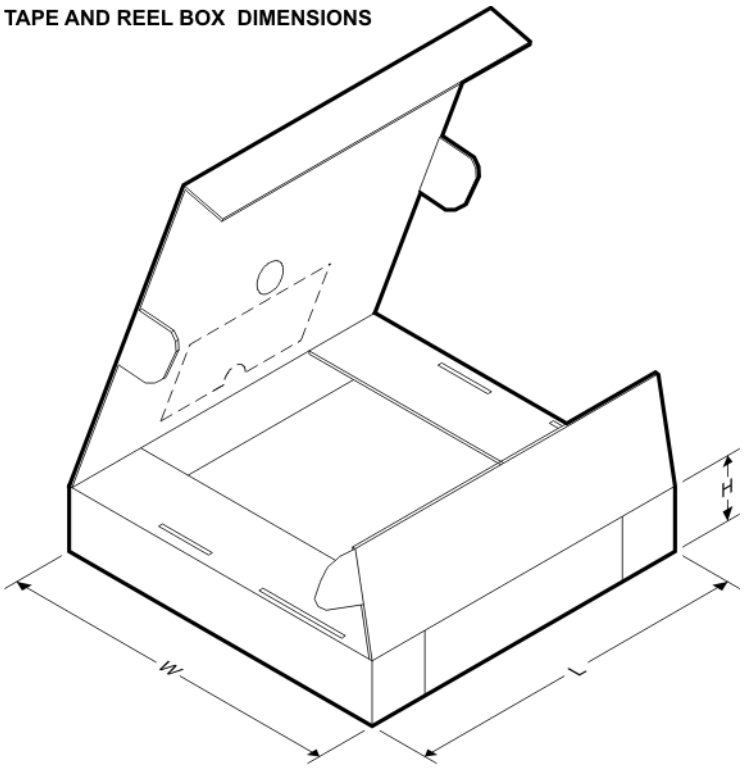
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC2G66DCTR	SM8	DCT	8	3000	177.8	12.4	3.45	4.4	1.45	4.0	12.0	Q3
SN74LVC2G66DCTR	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
SN74LVC2G66DCUR	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G66DCUR	VSSOP	DCU	8	3000	180.0	9.0	2.25	3.4	1.0	4.0	8.0	Q3
SN74LVC2G66DCUR	VSSOP	DCU	8	3000	178.0	9.5	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G66DCURG4	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G66DCUTG4	VSSOP	DCU	8	250	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G66YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

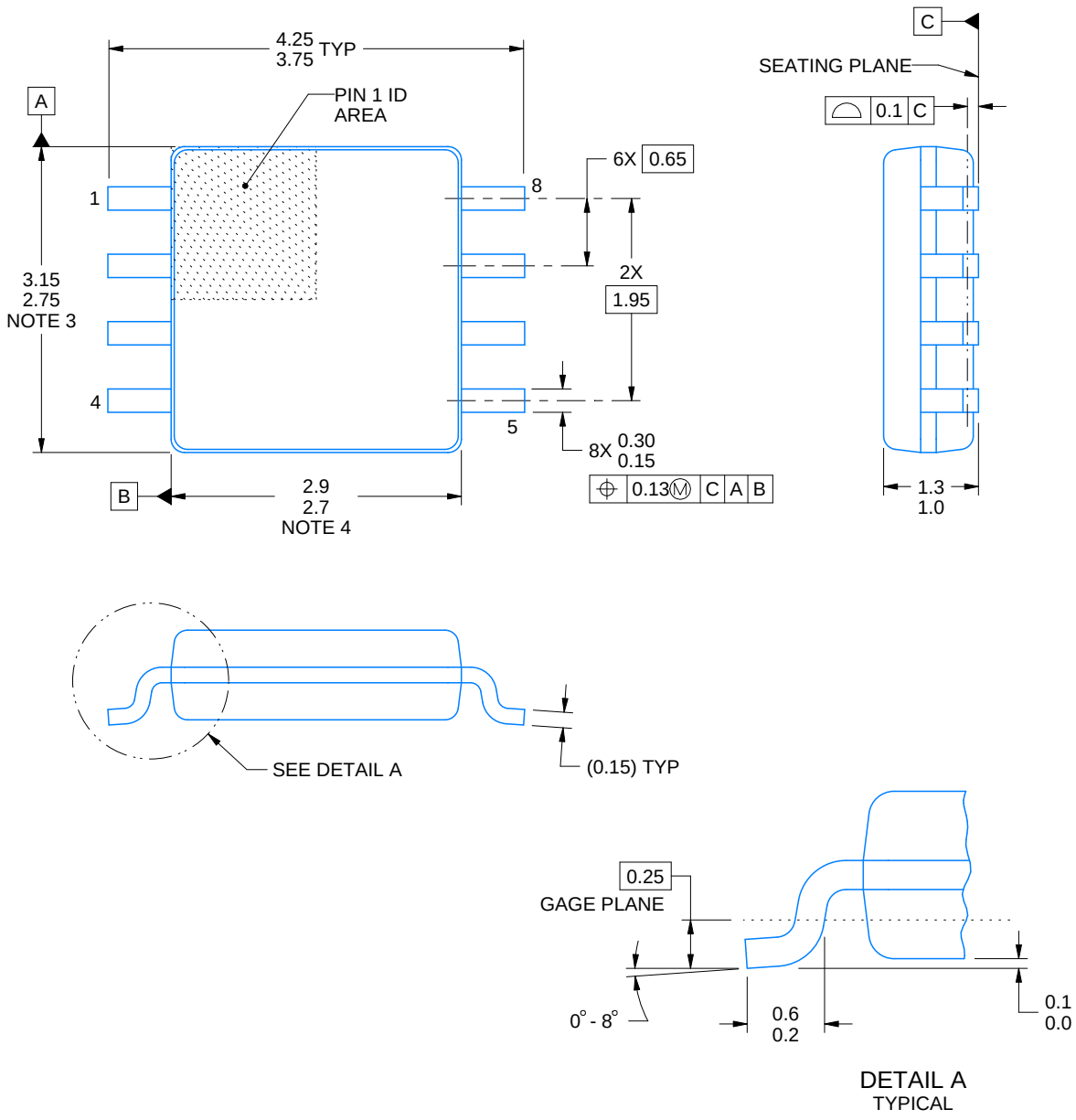
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC2G66DCTR	SM8	DCT	8	3000	183.0	183.0	20.0
SN74LVC2G66DCTR	SM8	DCT	8	3000	182.0	182.0	20.0
SN74LVC2G66DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC2G66DCUR	VSSOP	DCU	8	3000	182.0	182.0	20.0
SN74LVC2G66DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC2G66DCURG4	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC2G66DCUTG4	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC2G66YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0

PACKAGE OUTLINE

DCT0008A

SSOP - 1.3 mm max height

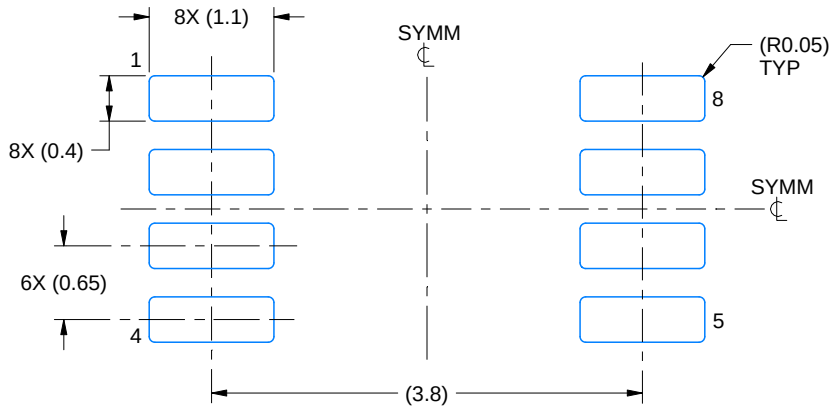
SMALL OUTLINE PACKAGE



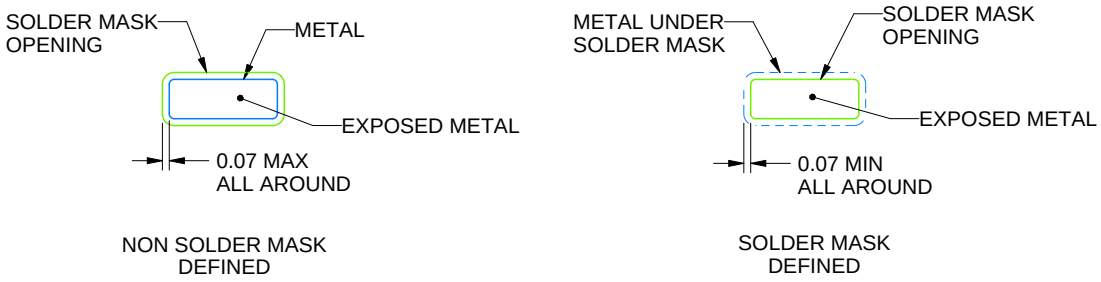
4220784/B 07/2020

NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MS-187.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X

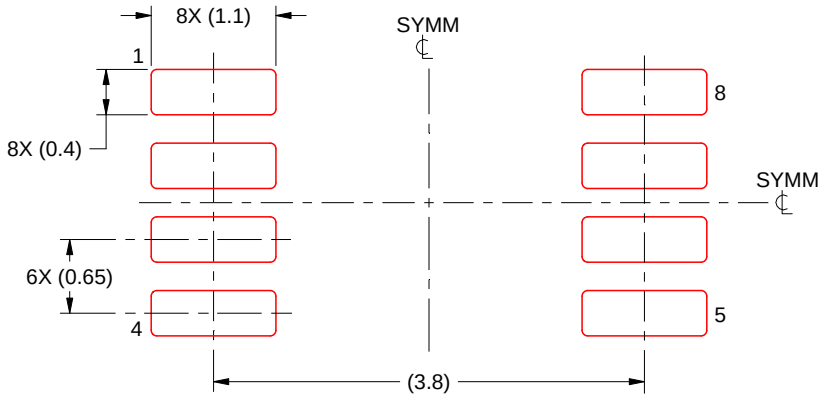


SOLDER MASK DETAILS

4220784/B 07/2020

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4220784/B 07/2020

NOTES: (continued)

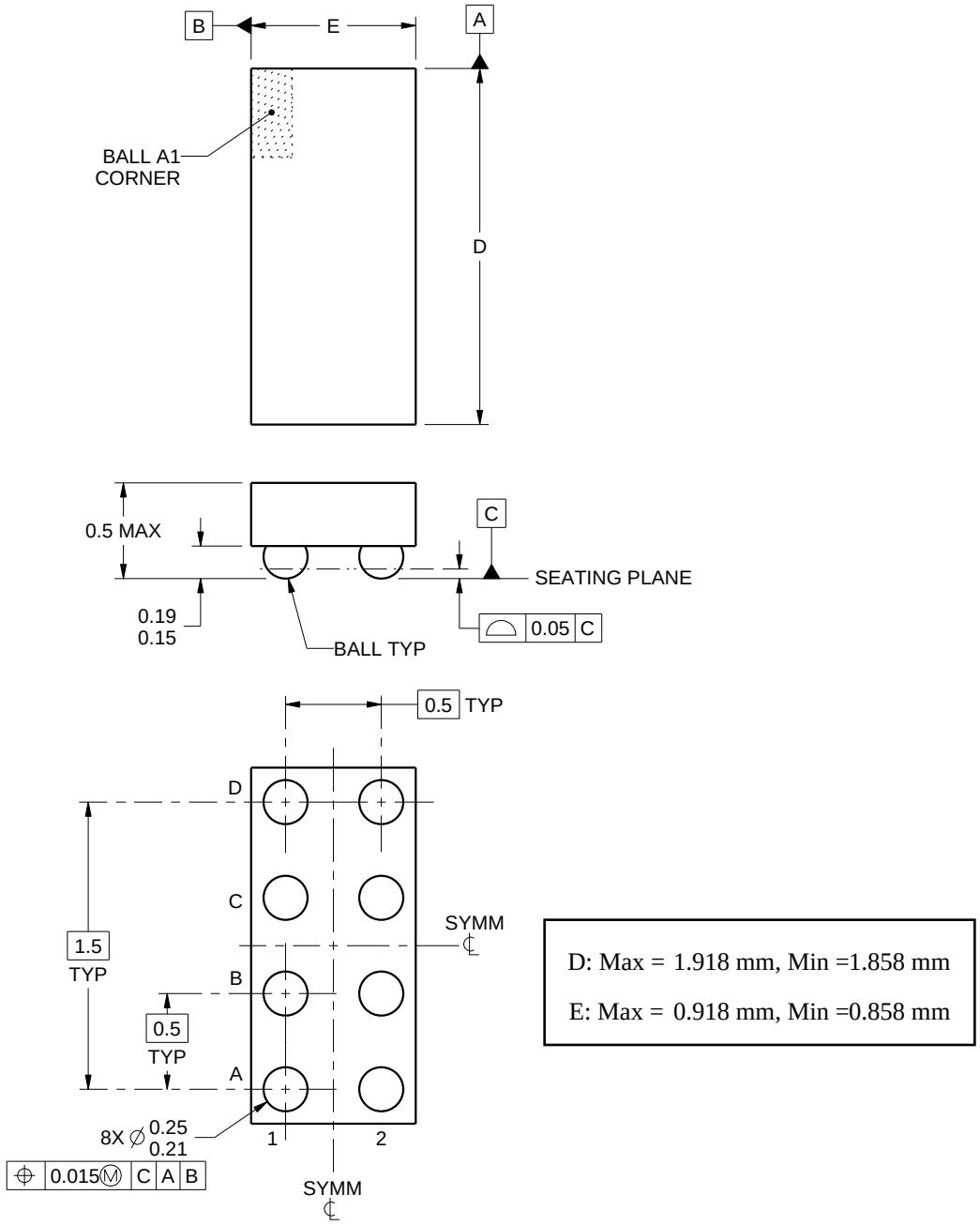
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

YZP0008

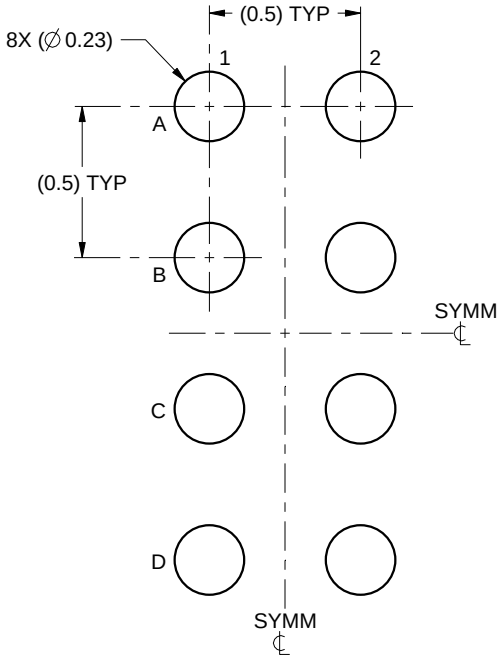
DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY

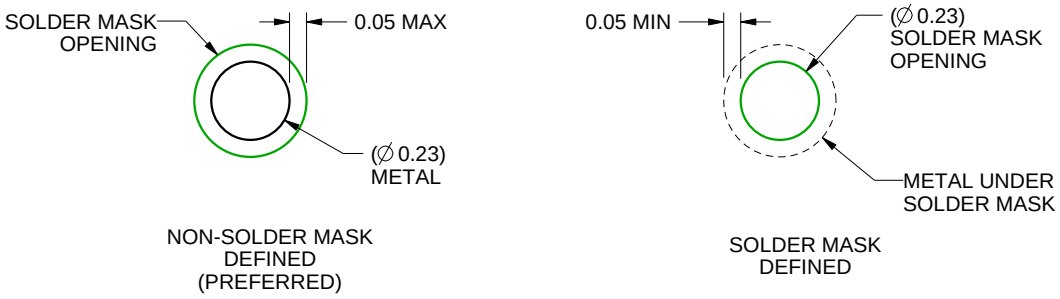


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
SCALE:40X

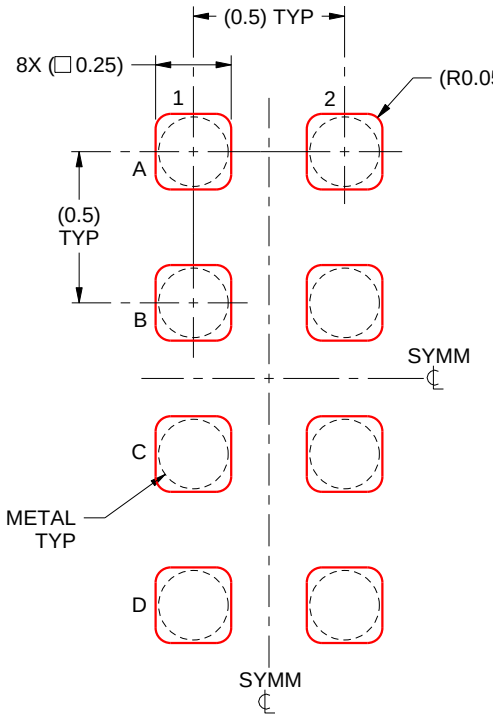


SOLDER MASK DETAILS
NOT TO SCALE

4223082/A 07/2016

NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



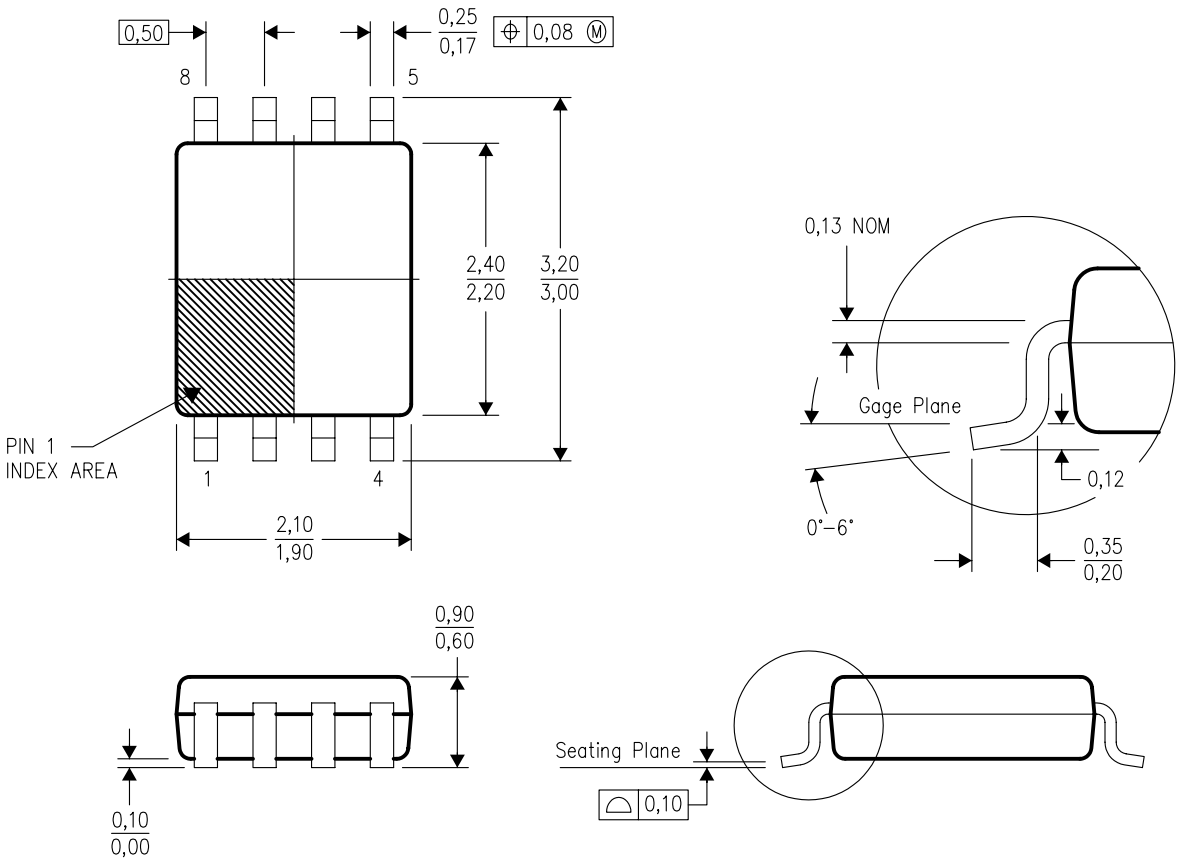
SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:40X

4223082/A 07/2016

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

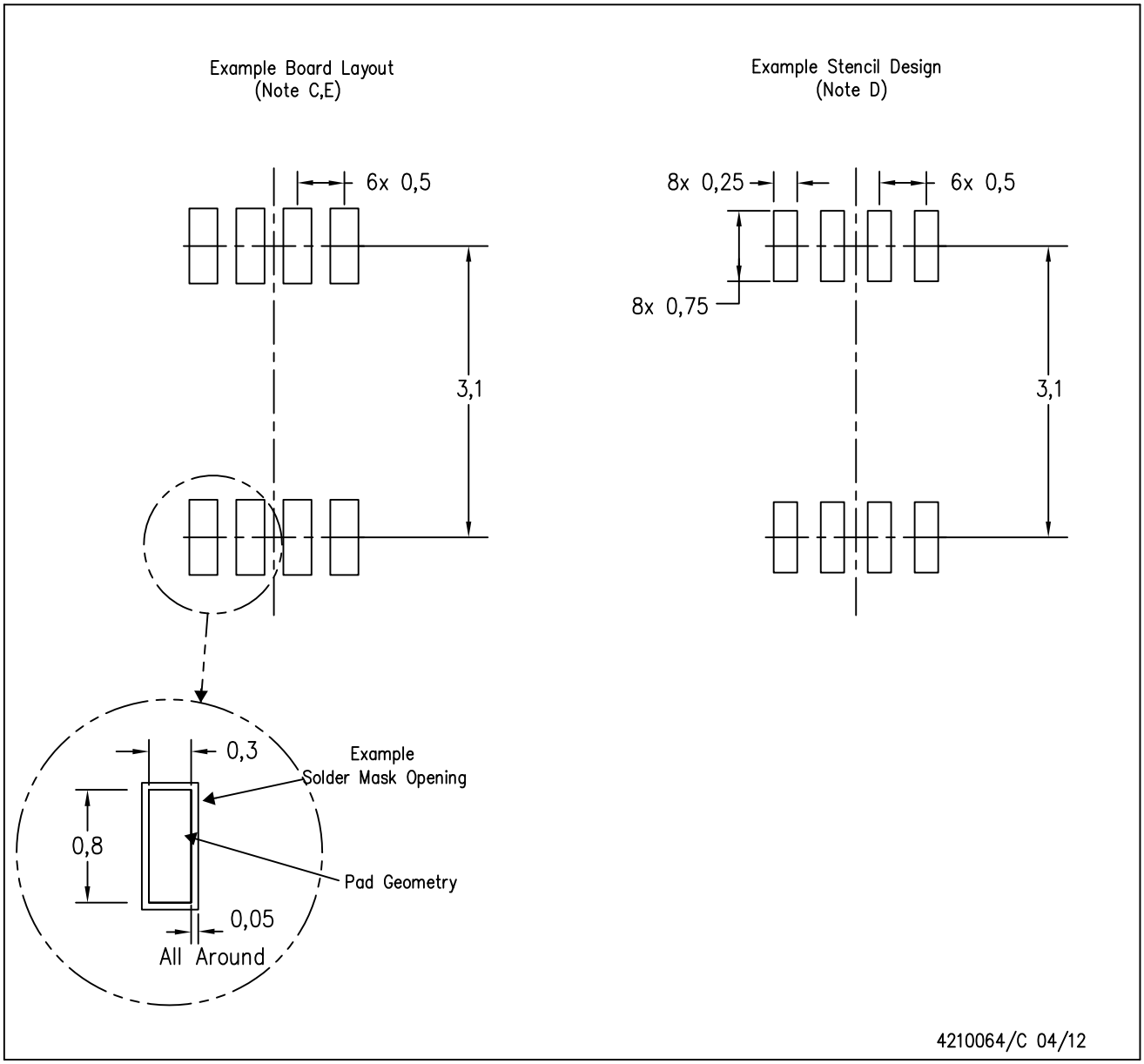
DCU (R–PDSO–G8) PLASTIC SMALL–OUTLINE PACKAGE (DIE DOWN)



4200503/F 07/05

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Falls within JEDEC MO–187 variation CA.

DCU (S–PDSO–G8) PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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